



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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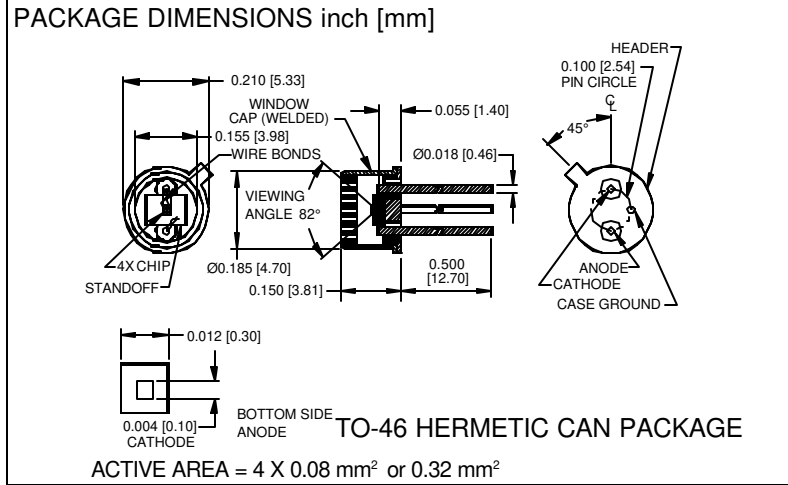
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PHOTONIC DETECTORS INC.

Silicon Carbide (SiC), Ultra Violet (U.V.) Photodiode Type PDU-S104



FEATURES

- 0.14 A/W @ 280 nm
- High shunt resistance
- 280 nm peak response
- Short wavelength resp.

DESCRIPTION

The **PDU-S104** is a SiC, planar passivated U.V. photodiode. Spectral range from 200 nm to 400 nm with a 0.08 mm² active area per chip. Four chips packaged in a isolated TO-46 with a U.V. transmitting window can.

APPLICATIONS

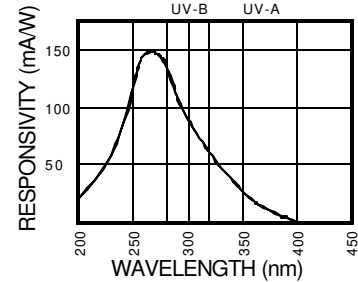
- Flame detectors
- U.V. sensors
- U.V. monitors
- U.V. instrumentation

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		20	V
T _{STG}	Storage Temperature	-55	+175	°C
T _O	Operating Temperature Range	-40	+125	°C
T _S	Soldering Temperature*		+240	°C
I _L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 1 SUN, 360 nm	30	40		nA
I _D	Dark Current	H = 0, V _R = 1 V		2	5	nA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	100	250		MΩ
TC R _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 0 V**		100	250	pF
λ _{range}	Spectral Application Range	Spot Scan	200		400	nm
λ _p	Spectral Response - Peak	Spot Scan		280		nm
V _{BR}	Breakdown Voltage	I = 10 μA	10	30		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		6x10 ⁻¹⁴		W/√Hz
tr	Response Time	RL = 1 KΩ V _R = 10 V		20	50	nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. ** f = 1MHz

[FORM NO. 100-PDU-S104 REV N/C]